

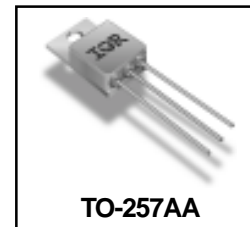
International
IR Rectifier
**RADIATION HARDENED
 POWER MOSFET
 THRU-HOLE (TO-257AA)**

PD - 91274D

**IRHY7130CM
 JANSR2N7380
 100V, N-CHANNEL
 REF: MIL-PRF-19500/614
 RAD-Hard™ HEXFET® TECHNOLOGY**

Product Summary

Part Number	Radiation Level	R _{DS(on)}	I _D	QPL Part Number
IRHY7130CM	100K Rads (Si)	0.18Ω	14.4A	JANSR2N7380
IRHY3130CM	300K Rads (Si)	0.18Ω	14.4A	JANSF2N7380
IRHY4130CM	600K Rads (Si)	0.18Ω	14.4A	JANSG2N7380
IRHY8130CM	1000K Rads (Si)	0.18Ω	14.4A	JANSH2N7380



International Rectifier's RADHard HEXFET® technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low R_{ds(on)} and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Low R_{DS(on)}
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	14.4	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	9.1	
I _{DM}	Pulsed Drain Current ①	58	
P _D @ T _C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	150	mJ
I _{AR}	Avalanche Current ①	—	A
E _{AR}	Repetitive Avalanche Energy ①	—	mJ
dv/dt	Peak Diode Recovery dv/dt ③	6.0	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in.(1.6mm) from case for 10s)	
	Weight	7.0 (Typical)	g

For footnotes refer to the last page

Electrical Characteristics @ T_J = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.11	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.18	Ω	V _{GS} = 12V, I _D = 9.1A ④
		—	—	0.20		V _{GS} = 12V, I _D = 14.4A
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	2.5	—	—	S (r̂)	V _{DS} > 15V, I _{DS} = 9.1A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	V _{DS} = 80V, V _{GS} = 0V
		—	—	250		V _{DS} = 80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	50	nC	V _{GS} = 12V, I _D = 14.4A
Q _{gs}	Gate-to-Source Charge	—	—	10		V _{DS} = 50V
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	20		
t _{d(on)}	Turn-On Delay Time	—	—	35	ns	V _{DD} = 50V, I _D = 14.4A V _{GS} = 12V, R _G = 7.5Ω
t _r	Rise Time	—	—	75		
t _{d(off)}	Turn-Off Delay Time	—	—	70		
t _f	Fall Time	—	—	60		
LS + LD	Total Inductance	—	7.0	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
C _{iss}	Input Capacitance	—	960	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{OSS}	Output Capacitance	—	340	—		
C _{rss}	Reverse Transfer Capacitance	—	85	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	14.4	A	
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	58		
V _{SD}	Diode Forward Voltage	—	—	1.8	V	T _J = 25°C, I _S = 14.4A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	275	nS	T _J = 25°C, I _F = 14.4A, di/dt ≤ 100A/μs
Q _{RR}	Reverse Recovery Charge	—	—	2.5	μC	V _{DD} ≤ 50V ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	1.67	°C/W	Typical socket mount
R _{thJA}	Junction-to-Ambient	—	—	80		

Note: Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

Radiation Characteristics

IRHY7130CM

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100K Rads(Si) ¹		300 - 1000K Rads (Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	100	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0	1.25	4.5		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	25	—	25	μA	V _{DS} =80V, V _{GS} =0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.18	—	0.24	Ω	V _{GS} = 12V, I _D =9.1A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-257AA)	—	0.18	—	0.24	Ω	V _{GS} = 12V, I _D =9.1A
V _{SD}	Diode Forward Voltage ④	—	1.8	—	1.8	V	V _{GS} = 0V, I _S = 14.4A

1. Part number IRHY7130, (JANSR2N7380)

2. Part numbers IRHY3130, IRHY4130 and IRHY8130 (JANSF2N7380, JANSNG2N7380 and JANSN2N7380)

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm ²)	Energy (MeV)	Range (μm)	V _{DS} (V)				
				@V _{GS} =0V	@V _{GS} =-5V	@V _{GS} =-10V	@V _{GS} =-15V	@V _{GS} =-20V
Cu	28	285	43	100	100	100	80	60
Br	36.8	305	39	100	90	70	50	—

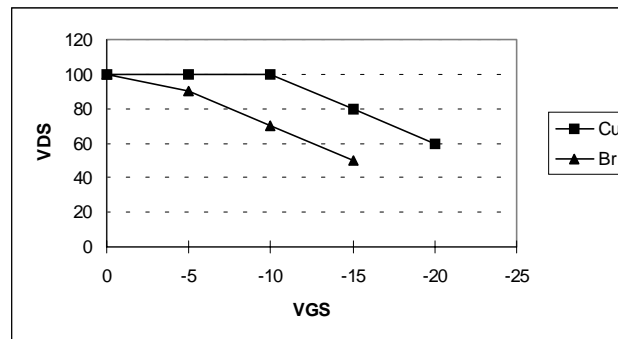


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

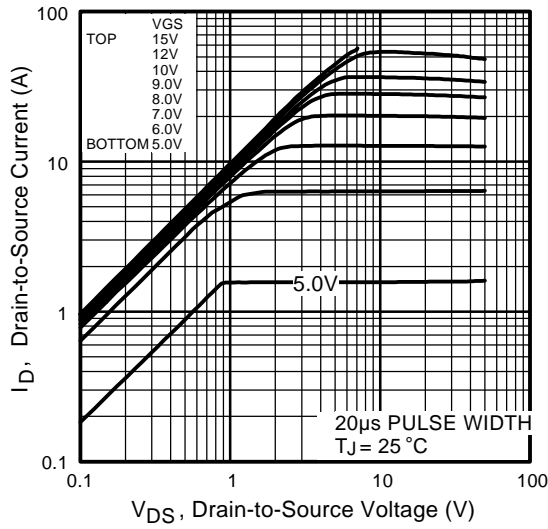


Fig 1. Typical Output Characteristics

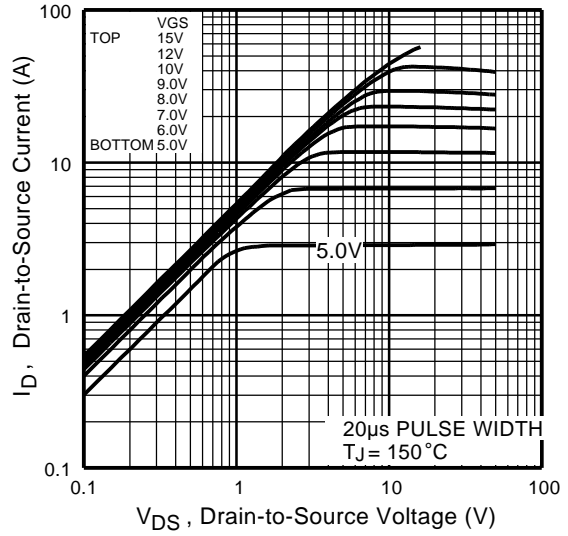


Fig 2. Typical Output Characteristics

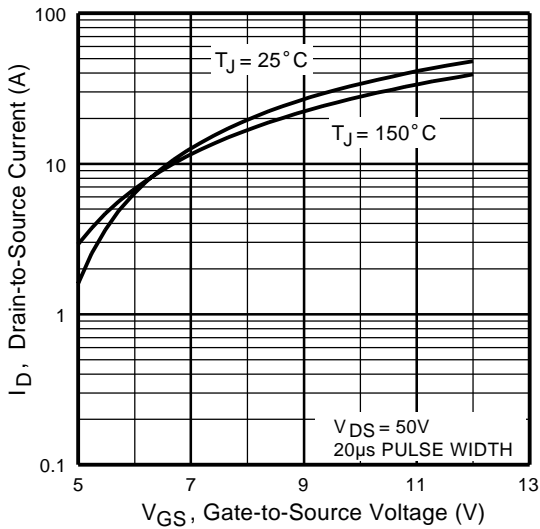


Fig 3. Typical Transfer Characteristics

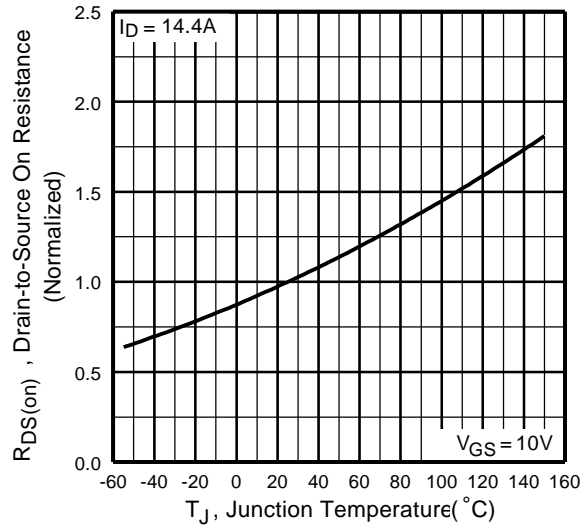


Fig 4. Normalized On-Resistance Vs. Temperature

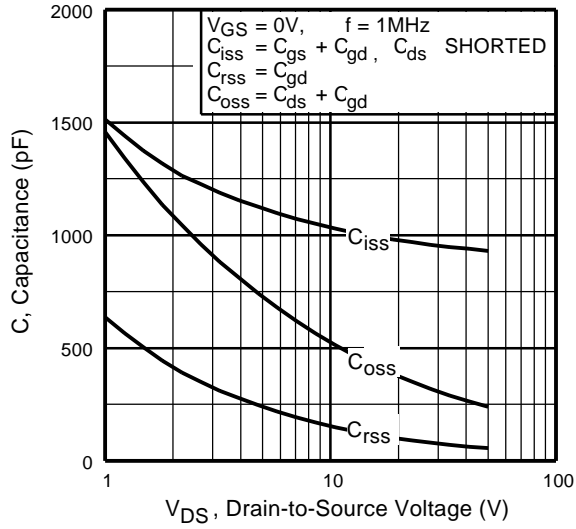


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

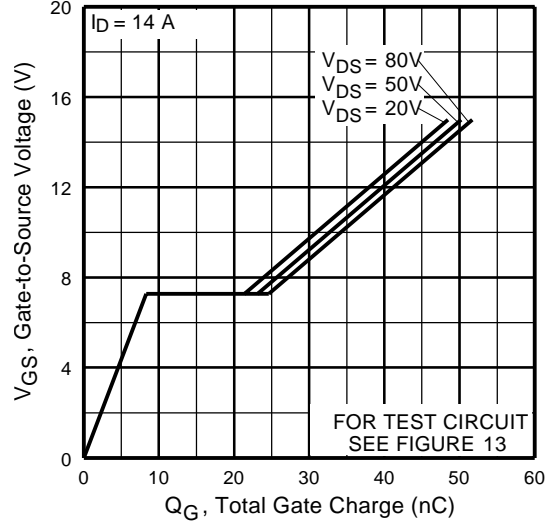


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

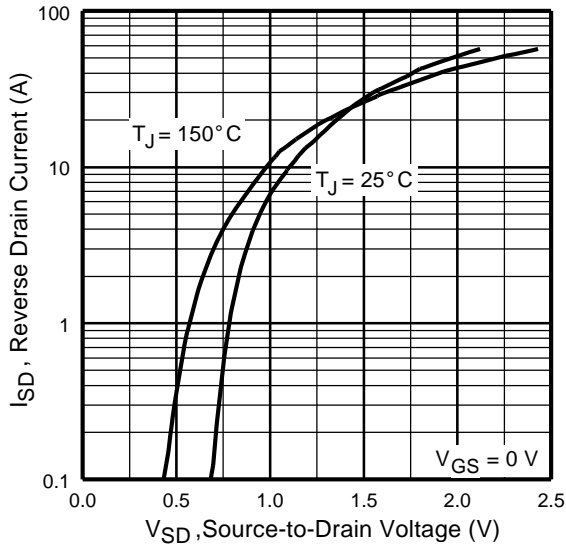


Fig 7. Typical Source-Drain Diode Forward Voltage

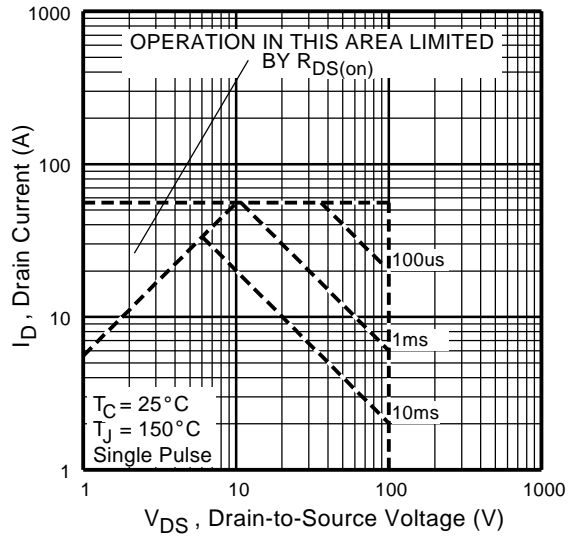


Fig 8. Maximum Safe Operating Area

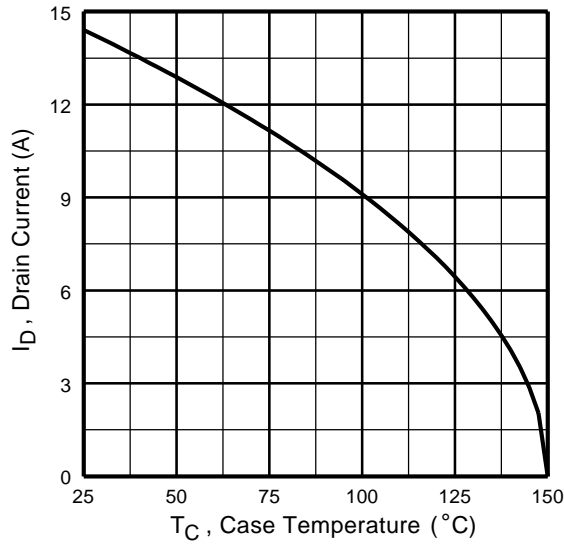


Fig 9. Maximum Drain Current Vs. Case Temperature

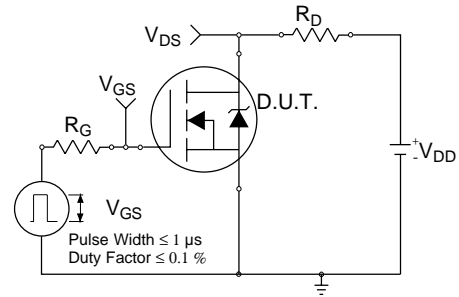


Fig10a. Switching Time Test Circuit

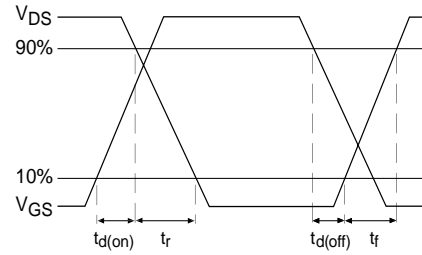


Fig 10b. Switching Time Waveforms

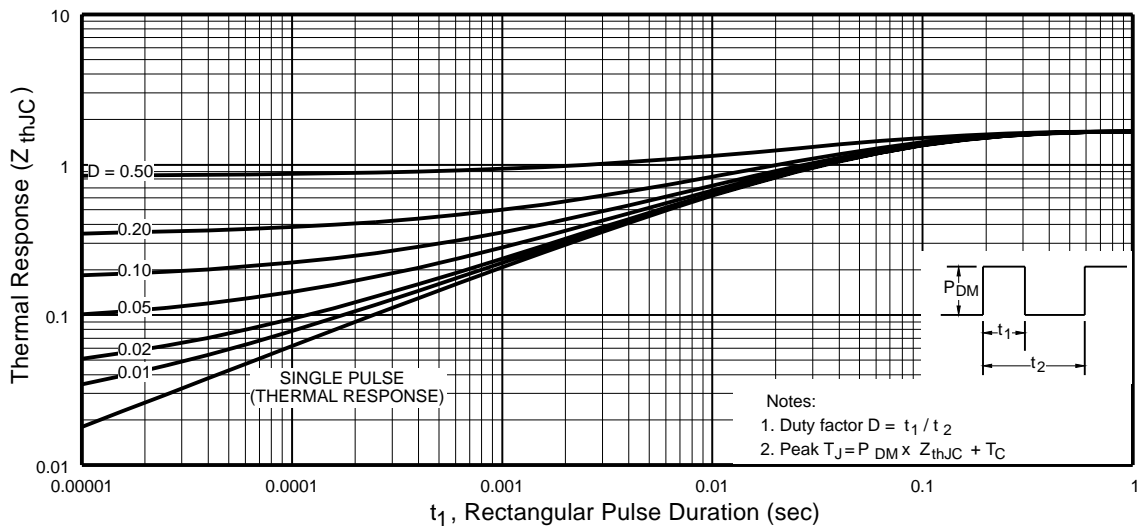


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

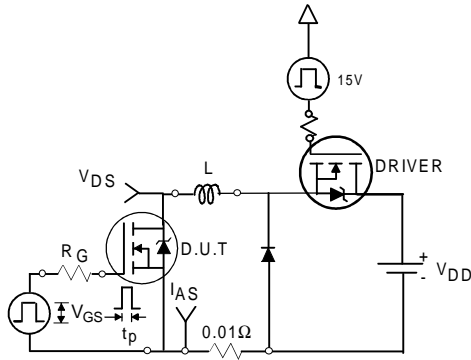


Fig 12a. Unclamped Inductive Test Circuit

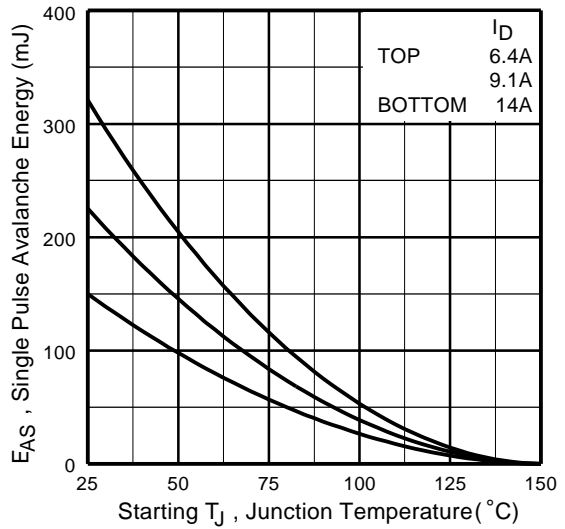


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

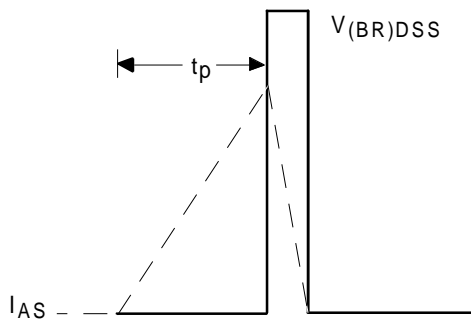


Fig 12b. Unclamped Inductive Waveforms

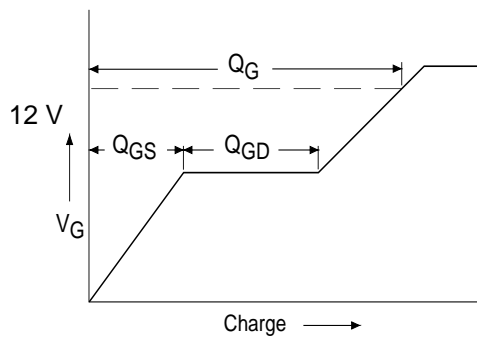


Fig13a. Basic Gate Charge Waveform

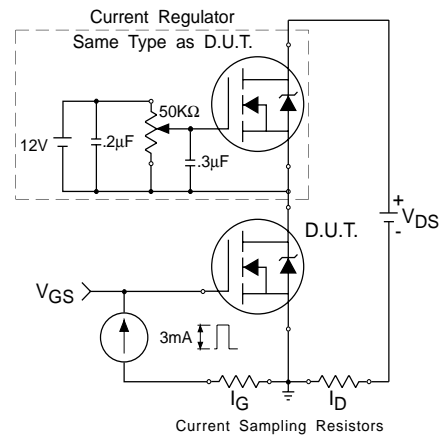


Fig 13b. Gate Charge Test Circuit

